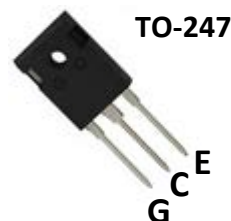


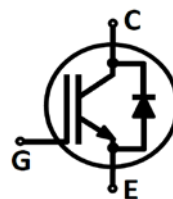
特征

饱和压降为正温度系数，易于并联使用
内置快恢复二极管
高可靠性及热稳定性，良好的参数一致性
极低的关断损耗



应用领域

逆变焊机、UPS等



最大额定值¹

参数	符号	额定值	单位
集电极-发射极电压	V_{CE}	1200	V
集电极电流 $T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$	I_C	50 ² 25	A
集电极脉冲电流	I_{Cpuls}	75* ³	
RBSOA电流 $V_{CE}<1200\text{V}, T_j<150^\circ\text{C}$	I_{Cpeak}	75*	
二极管正向电流 $T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$	I_F	50 ² 15 ²	
二极管脉冲电流	I_{Fpuls}	45*	
栅极-发射极电压	V_{GE}	± 20	V
耗散功率 $T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$	P_{tot}	216 86	W
工作结温	T_j	-55~150	°C
储存温度	T_{stg}	-55~150	

¹测试标准参考JESD-022

²受限于邦定线

³加*表示估计值，下同

⁴允许短路次数:<1000;短路时间间隔:>1s

热学特性

参数	符号	封装形式	最小值	典型值	最大值	单位
IGBT结壳热阻	R_{thJC}	TO-247	-	-	0.58	K/W
二极管结壳热阻	R_{thJCD}	TO-247	-	-	1.5	
结-环境热阻	R_{thJA}	TO-247	-	-	40	

电学特性 (未特殊说明时, $T_j=25^\circ\text{C}$)

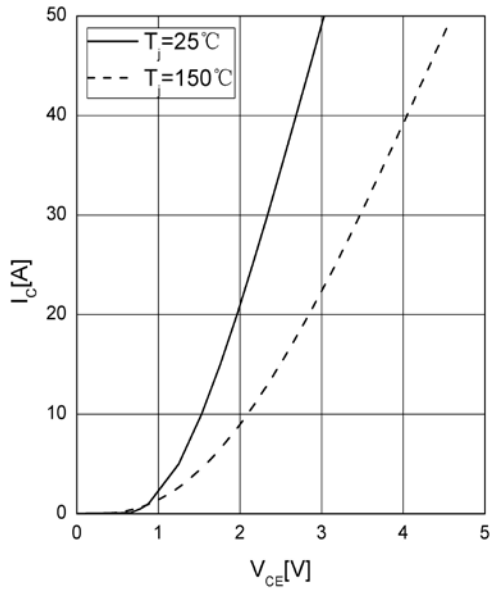
参数	符号	测试条件	最小值	典型值	最大值	单位
静态特性						
击穿电压	$V_{(BR)CES}$	$V_{GE}=0V, I_C=0.5mA$	1200	-	-	V
IGBT导通压降	$V_{CE(sat)}$	$V_{GE}=15V, I_C=25A$	-	2.1	2.8	
		$T_j=150^\circ\text{C}$	-	3.2	-	
二极管正向压降	V_F	$V_{GE}=0V, I_F=25A$	-	4.7	-	
		$T_j=150^\circ\text{C}$	-	4.1	-	
阈值电压	$V_{GE(th)}$	$I_C=1mA, V_{CE}=V_{GE}$	5	6.1	6.5	
集电极-发射极漏电流	I_{CES}	$V_{CE}=1200V, V_{GE}=0V$	-	-	0.1	mA
		$T_j=150^\circ\text{C}$	-	-	2	
栅极-发射极漏电流	I_{GES}	$V_{CE}=0V, V_{GE}=20V$	-	-	200	nA
动态特性						
输入电容	C_{iss}	$V_{CE}=25V$	-	2750	-	pF
输出电容	C_{oss}	$V_{GE}=0V$	-	85	-	
反馈电容	C_{rss}	$f=1MHz$	-	48	-	
栅电荷	Q_G	$V_{CC}=600V, I_C=25A, V_{GE}=15V$	-	117	-	nC

参数	符号	测试条件	最小值	典型值	最大值	单位
IGBT开关特性 (感性负载)						
开通延迟时间	$t_{d(on)}$	$T_j=25^\circ\text{C}$ $V_{CC}=600\text{V}, I_C=25\text{A}$ $V_{GE}=15/0\text{V}$ $R_G=15\Omega$ $L_{load}=500\mu\text{H}$	-	32	-	ns
上升时间	t_r		-	54	-	
关断延迟时间	$t_{d(off)}$		-	175	-	
下降时间	t_f		-	40	-	
开通损耗	E_{on}	$R_G=15\Omega$ $L_{load}=500\mu\text{H}$	-	1.4	-	mJ
关断损耗	E_{off}		-	0.6	-	
开关损耗	E_{ts}		-	2.0	-	
开通延迟时间	$t_{d(on)}$	$T_j=150^\circ\text{C}$ $V_{CC}=600\text{V}, I_C=25\text{A}$ $V_{GE}=15/0\text{V}$ $R_G=15\Omega$ $L_{load}=500\mu\text{H}$	-	29	-	ns
上升时间	t_r		-	49	-	
关断延迟时间	$t_{d(off)}$		-	200	-	
下降时间	t_f		-	57	-	
开通损耗	E_{on}	$R_G=15\Omega$ $L_{load}=500\mu\text{H}$	-	1.4	-	mJ
关断损耗	E_{off}		-	0.7	-	
开关损耗	E_{ts}		-	2.1	-	
二极管开关特性						
反向恢复时间	t_{rr}	$T_j=25^\circ\text{C}$ $V_R=600\text{V}, I_F=25\text{A}$ $di_F/dt=600\text{A}/\mu\text{s}$	-	58	-	ns
反向恢复电荷	Q_{rr}		-	1.1	-	μC
反向恢复峰值 电流	I_{rrm}		-	32	-	A
反向恢复时间	t_{rr}	$T_j=150^\circ\text{C}$ $V_R=600\text{V}, I_F=25\text{A}$ $di_F/dt=600\text{A}/\mu\text{s}$	-	78	-	ns
反向恢复电荷	Q_{rr}		-	1.8	-	μC
反向恢复峰值 电流	I_{rrm}		-	39	-	A

输出特性 IGBT

output characteristic IGBT

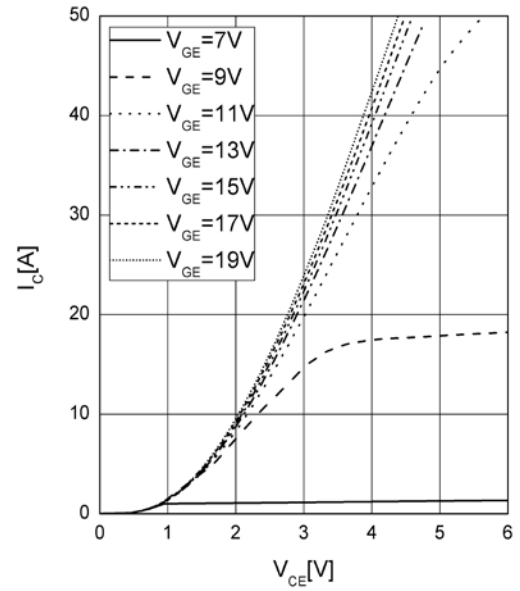
$I_c = f(V_{CE}), V_{GE} = 15V$



输出特性 IGBT

output characteristic IGBT

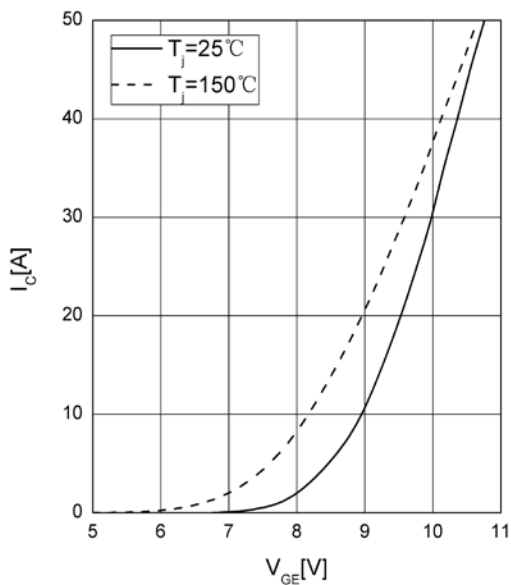
$I_c = f(V_{CE}), T_j = 150^\circ C$



传输特性 IGBT

transfer characteristic IGBT

$I_c = f(V_{GE}), V_{CE} = 20V$

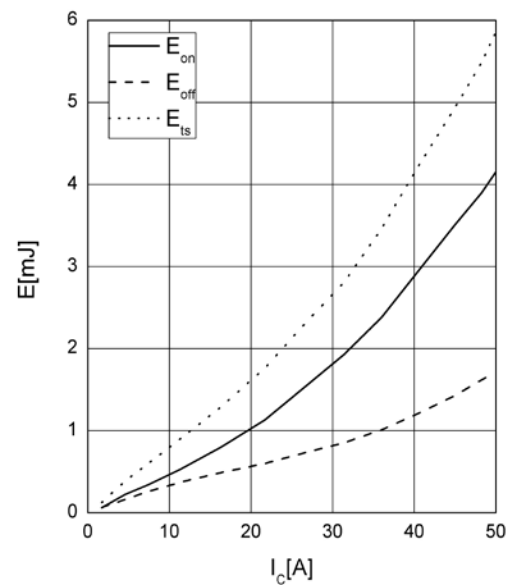


开关损耗 IGBT

switching losses IGBT

$E_{on} = f(I_c), E_{off} = f(I_c), E_{ts} = f(I_c)$

$V_{GE} = 15/0V, R_G = 15\Omega, V_{CE} = 600V, T_j = 150^\circ C$

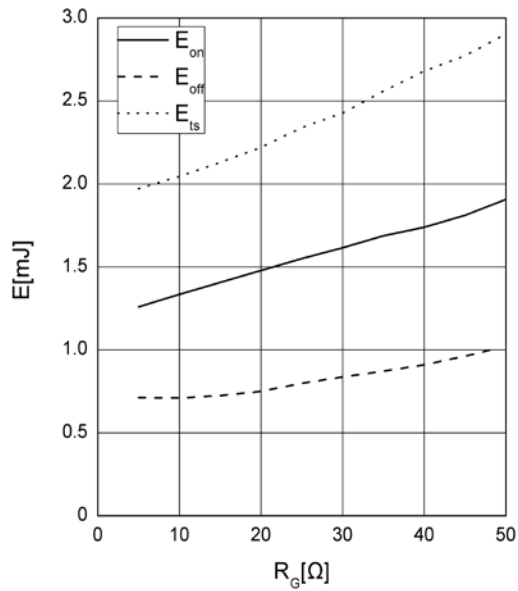


开关损耗 IGBT

switching losses IGBT

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$, $E_{ts} = f(R_G)$

$V_{GE} = 15/0\text{ V}$, $I_C = 25\text{ A}$, $V_{CE} = 600\text{ V}$, $T_J = 150^\circ\text{C}$

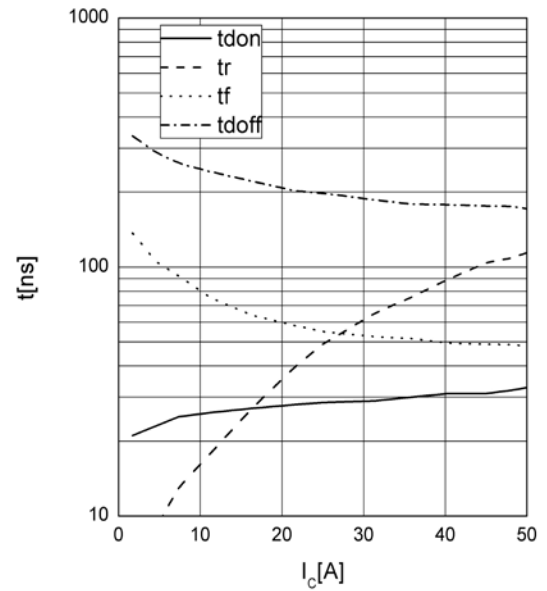


开关时间 IGBT

switching times IGBT

$t_{d(on)} = f(I_C)$, $t_r = f(I_C)$, $t_f = f(I_C)$, $t_{d(off)} = f(I_C)$

$V_{GE} = 15/0\text{ V}$, $R_G = 15\ \Omega$, $V_{CE} = 600\text{ V}$, $T_J = 150^\circ\text{C}$

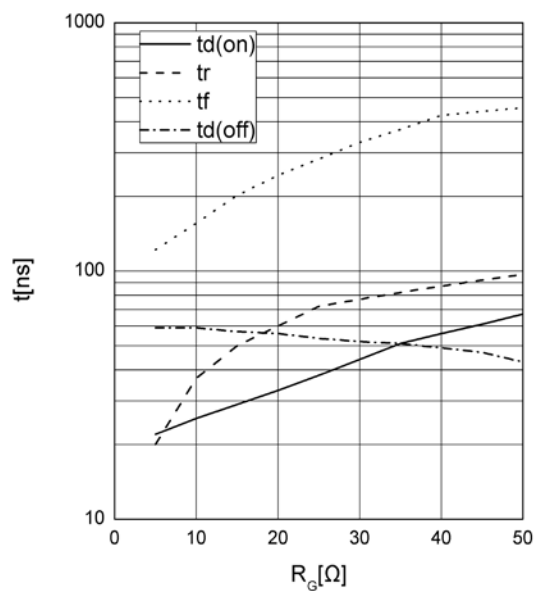


开关时间 IGBT

switching times IGBT

$t_{d(on)} = f(R_G)$, $t_r = f(R_G)$, $t_f = f(R_G)$, $t_{d(off)} = f(R_G)$

$V_{GE} = 15/0\text{ V}$, $I_C = 25\text{ A}$, $V_{CE} = 600\text{ V}$, $T_J = 150^\circ\text{C}$

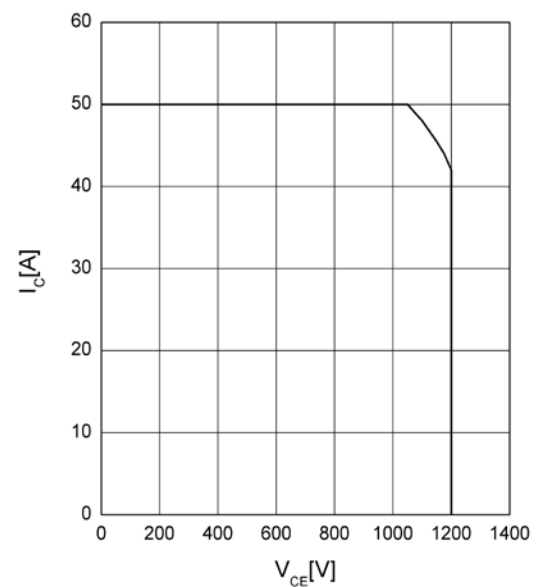


反偏安全工作区 IGBT

reverse bias safe operating area IGBT

$I_C = f(V_{CE})$

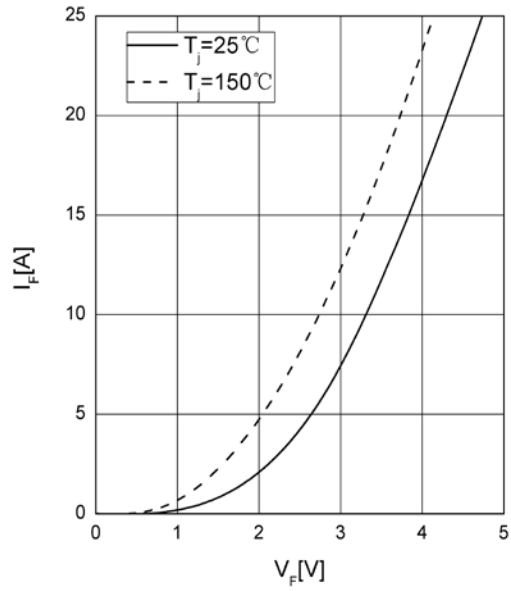
$V_{GE} = 15/0\text{ V}$, $R_{Goff} = 15\ \Omega$, $T_J = 150^\circ\text{C}$



正向偏压特性 二极管

forward characteristic of Diode

$I_F = f(V_F)$



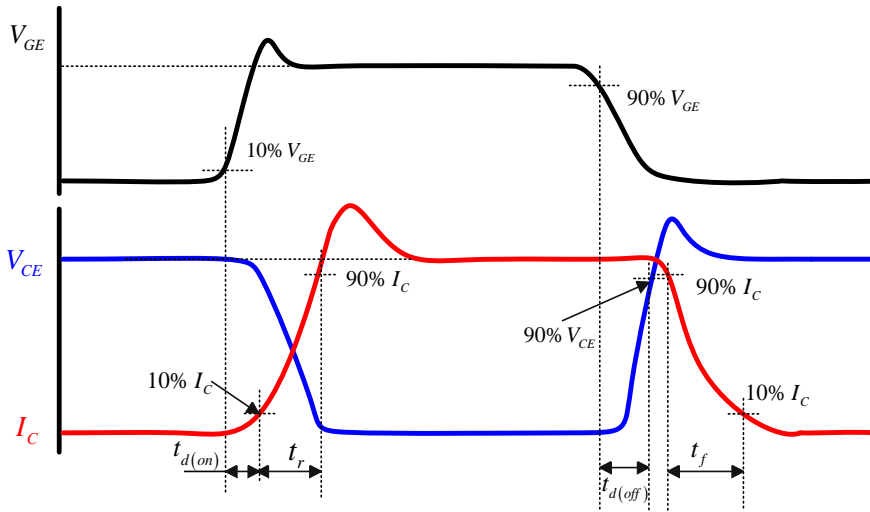


Figure A. Definition of switching times

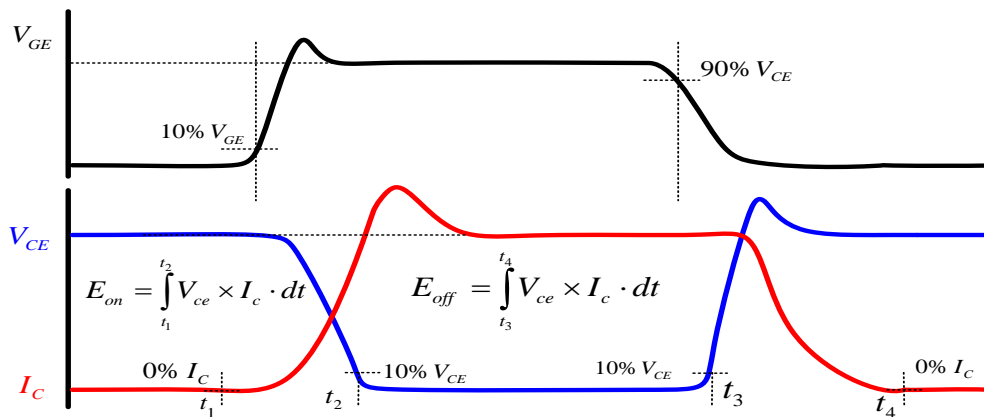


Figure B. Definition of switching losses

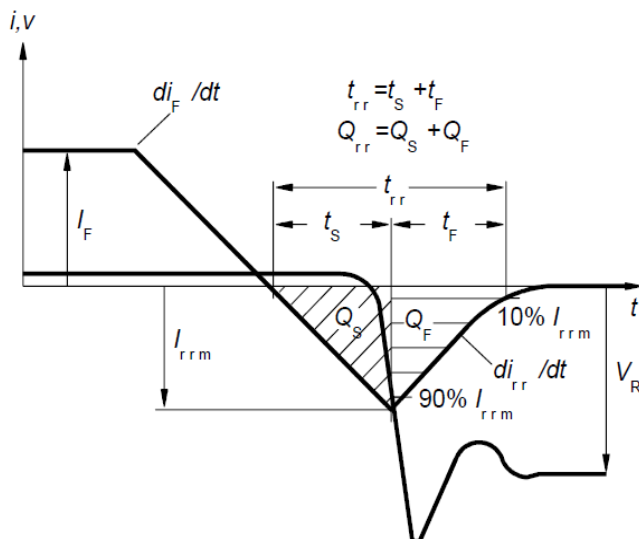


Figure C. Definition of diodes switching characteristics

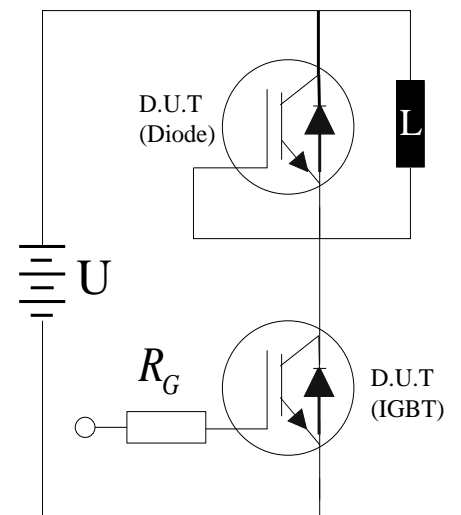
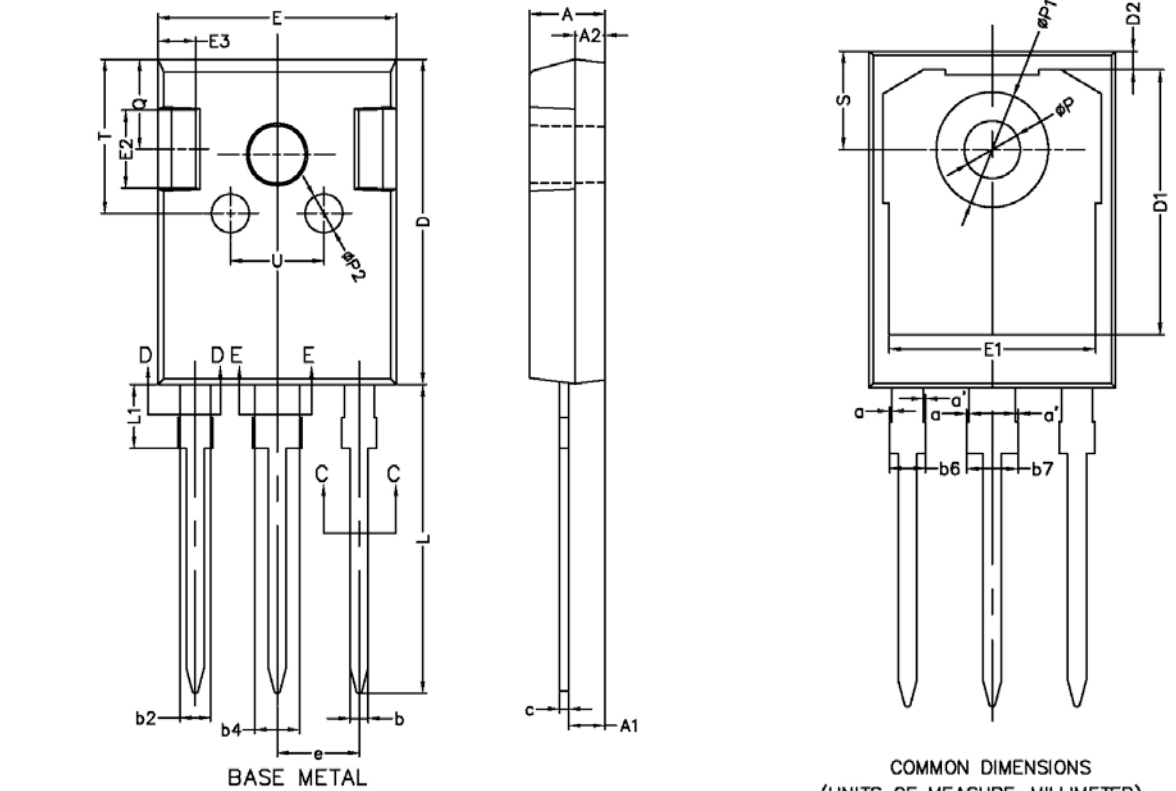


Figure D. Dynamic test circuit

TO-247



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
△ a	0	—	0.15
△ a'	0	—	0.15
b	1.16	—	1.26
b1	1.15	1.2	1.22
b2	1.96	—	2.06
b3	1.95	2.00	2.02
b4	2.96	—	3.06
b5	2.95	3.00	3.02
△ b6	—	—	2.25
△ b7	—	—	3.25
c	0.59	—	0.66
c1	0.58	0.60	0.62
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.20	1.35
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
△ e	5.34	5.44	5.54
L	19.80	19.92	20.10
L1	—	—	4.30
P	3.50	3.60	3.70
P1	—	—	7.40
P2	2.40	2.50	2.60
Q	5.60	—	6.00
△ S	6.05	6.15	6.25
T	9.80	—	10.20
U	6.00	—	6.40

NOTES:
1. ALL DIMENSIONS REFER TO JEDEC STANDARD TO-247 AD DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.
2. EJECTION MARK DEPTH 0.10 ± 0.15

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [IGBT Transistors](#) category:

Click to view products by [JUNSHINE](#) manufacturer:

Other Similar products are found below :

[748152A](#) [FGH60T65SHD_F155](#) [APT100GT60B2RG](#) [APT13GP120BG](#) [APT20GN60BG](#) [APT20GT60BRDQ1G](#) [APT25GN120B2DQ2G](#)
[APT35GA90BD15](#) [APT36GA60BD15](#) [APT40GP60B2DQ2G](#) [APT40GP90B2DQ2G](#) [APT50GN120B2G](#) [APT50GT60BRG](#)
[APT64GA90B2D30](#) [APT70GR120J](#) [NGTB10N60FG](#) [NGTB30N60L2WG](#) [NGTG25N120FL2WG](#) [IGP30N60H3XKSA1](#) [STGB15H60DF](#)
[STGFW20V60DF](#) [STGFW30V60DF](#) [STGFW40V60F](#) [STGWA25H120DF2](#) [FGB3236_F085](#) [APT25GN120BG](#) [APT25GR120S](#)
[APT30GN60BDQ2G](#) [APT30GN60BG](#) [APT30GP60BG](#) [APT30GS60BRDQ2G](#) [APT30N60BC6](#) [APT35GP120JDQ2](#) [APT36GA60B](#)
[APT45GR65B2DU30](#) [APT50GP60B2DQ2G](#) [APT68GA60B](#) [APT70GR65B](#) [APT70GR65B2SCD30](#) [GT50JR22\(STA1ES\)](#) [TIG058E8-TL-H](#)
[IDW40E65D2](#) [SGB15N120ATMA1](#) [NGTB50N60L2WG](#) [STGB10H60DF](#) [STGB20V60F](#) [STGB40V60F](#) [STGFW80V60F](#)
[IGW40N120H3FKSA1](#) [RJH60D7BDPQ-E0#T2](#)